



High-end Power Semiconductor Manufacturer

ZP4300A 5100-6500V

Standard Rectifier Diode

- High power cycling capability
- Low on-state and switching losses
- Optimized for line frequency rectifiers
- Designed for traction and industrial applications



Average forward current					I_{FAV}	4380 A				
Repetitive peak reverse voltage					V_{RRM}	5100–6500 V				
V_{RRM} , V	5100	5200	5400	5600	5800	6000	6200	6400	6500	
Voltage code	51	52	54	56	58	60	62	64	65	
T_j , °C	-60 – 150									

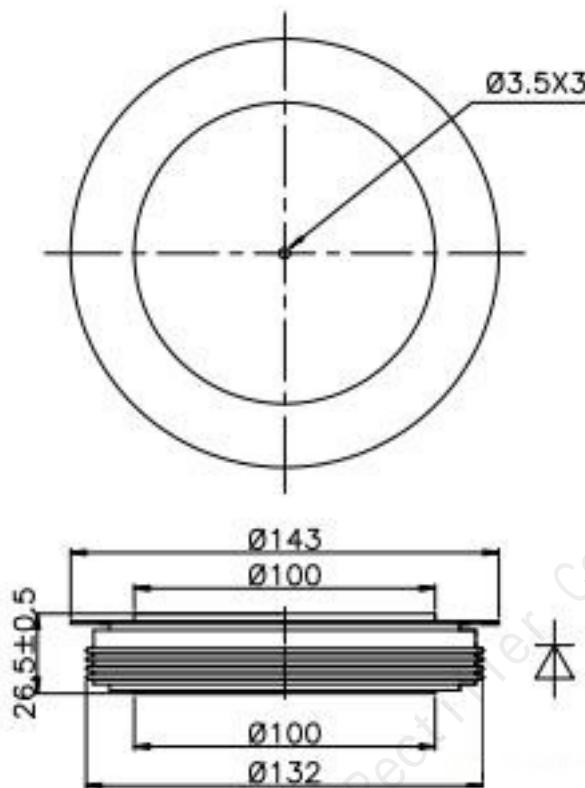
MAXIMUM ALLOWABLE RATINGS

Symbols and parameters		Units	Values	Test conditions	
ON-STATE					
I_{FAV}	Average forward current	A	4380	$T_c=100$ °C; Double side cooled; 180° half-sine wave; 50 Hz	
I_{FSM}	Surge forward current	kA	57.0	$T_j=T_{j\max}$	180° half-sine wave; ($t_p=10$ ms); $V_R=0.6V_{RRM}$
I^2t	Safety factor	$A^2s \cdot 10^3$	16200	$T_j=T_{j\max}$	180° half-sine wave; ($t_p=10$ ms); $V_R=0.6V_{RRM}$
BLOCKING					
V_{RRM}	Repetitive peak reverse voltages	V	4300-5000	$t_p=10$ ms; $T_j=T_{j\max}$	
THERMAL					
T_{stg}	Storage temperature	°C	-40-160		
T_j	Operating junction temperature	°C	-60-150		
MECHANICAL					
F	Mounting force	kN	81.0-108.0		

CHARACTERISTICS

Symbols and parameters		Units	Values	Conditions
ON-STATE				
V _{FM}	Peak forward voltage, max	V	1.70	T _j =25 °C; I _{FM} =5000 A; F=108kN
V _{F(TO)}	Forward threshold voltage, max	V	0.88	
r _T	Forward slope resistance, max	mΩ	0.16	T _j =T _{j max} ;
BLOCKING				
I _{RRM}	Repetitive peak reverse current, max	mA	300	T _j =T _{j max} ; V _R =V _{RRM}
THERMAL				
R _{thjc}	Thermal resistance, junction to case, max	°C/W	0.0057	At 180° sine; double side cooled Clamping force 108kN
R _{thck}	Thermal resistance, case to heatsink, max	°C/W	0.0015	
MECHANICAL				
w	Weight, typ	g	2020	

OVERALL DIMENSIONS



ZT110

All dimensions in millimeters

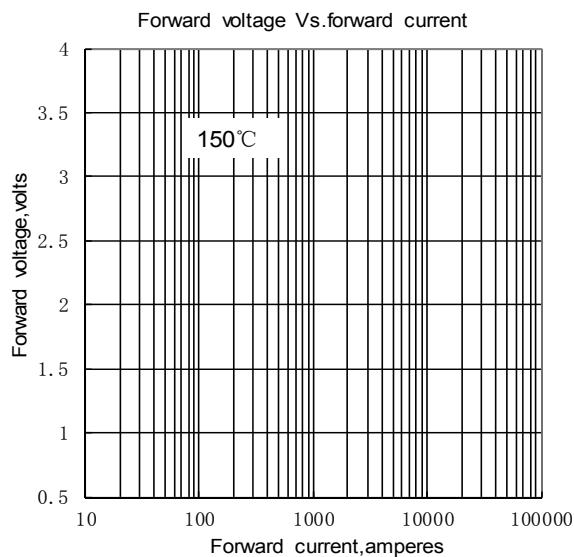


Fig.1

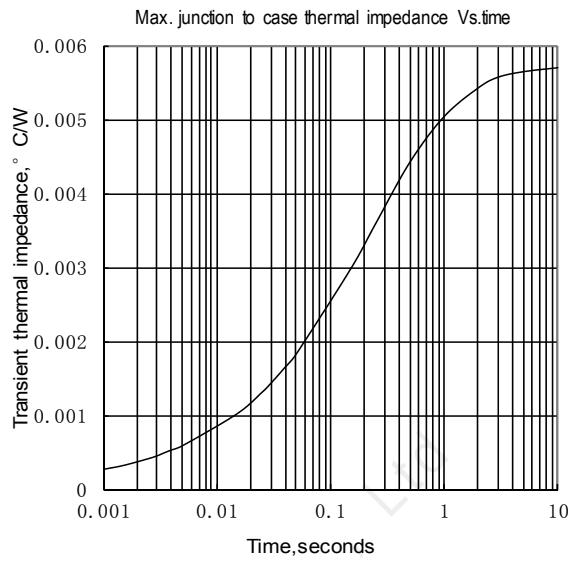


Fig.2

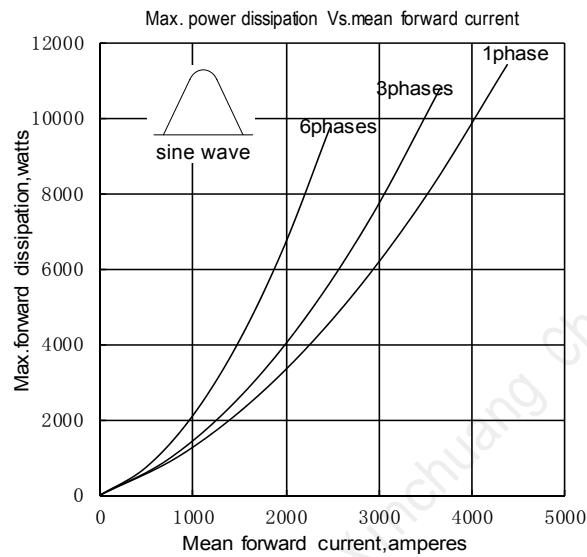


Fig.3

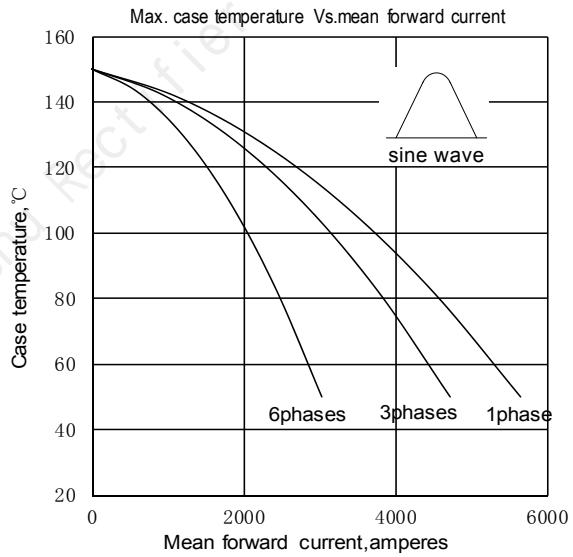
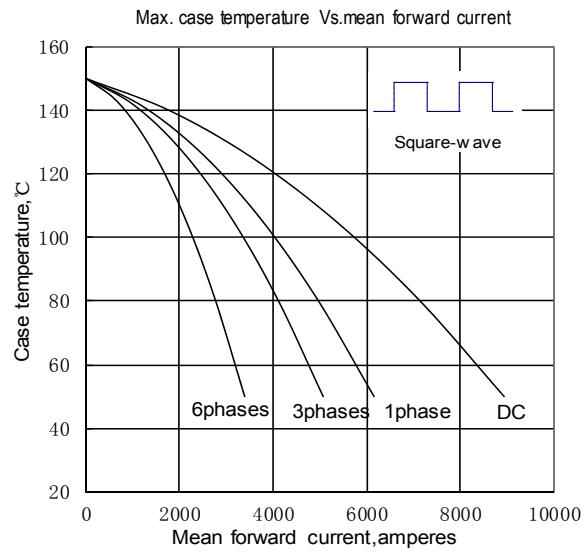
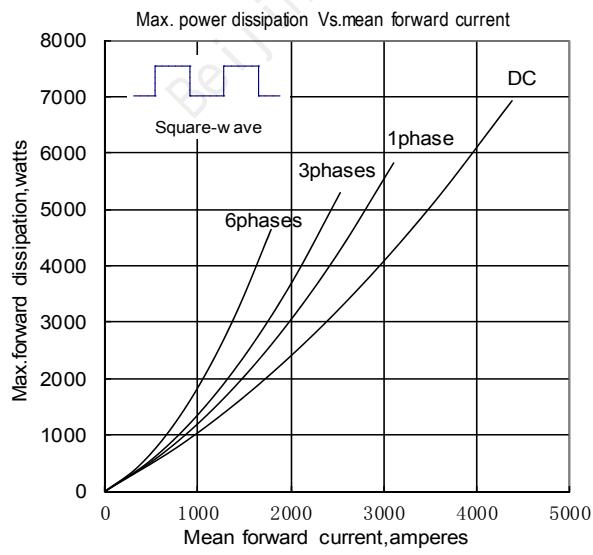


Fig.4



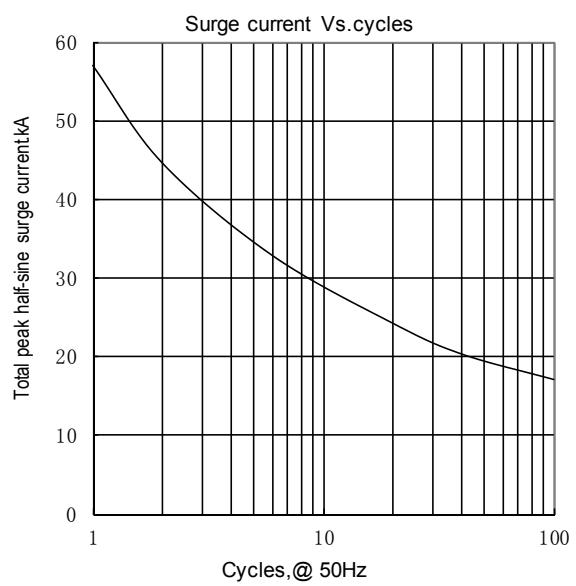


Fig.7

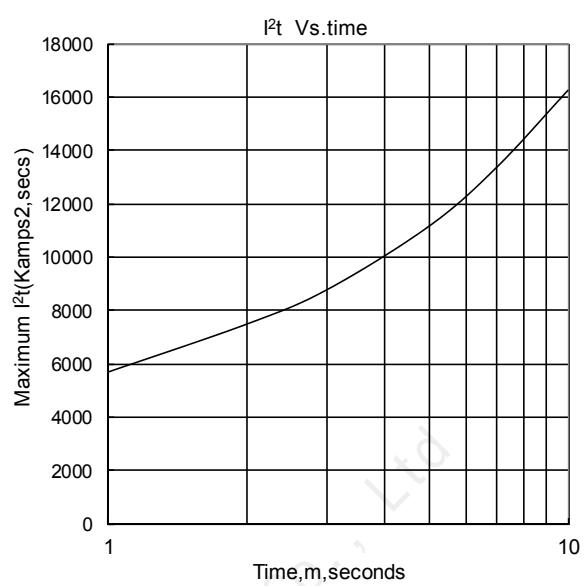


Fig.8